

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No. 040373/0300

#9/a
6/10/2
Jmlr

Applicant: Toshiyuki HIROTA et al.

Title: SEMICONDUCTOR DEVICE WITH HIGH- AND LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE

Serial No.: 09/741,195

Filed: December 21, 2000

Examiner: Vu, Quang D.

Art Unit: 2811



AMENDMENT AND REPLY TO 37 C.F.R. §1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In reply to the Office Action dated February 19, 2002, please amend the application as follows:

IN THE DRAWINGS:

By way of a separate letter submitted herewith, Applicants propose to amend Figure 1, as indicated in red on the attached sheet. With the Examiner's approval, these changes will be incorporated into the formal drawings in due course.

IN THE SPECIFICATION:

Please amend the specification as follows. The changes to the specification are shown explicitly in the attached "Version with Markings to Show Changes Made."

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